## **UV Enhanced Series**

Inversion Layer and Planar Diffused Silicon Photodiodes

OSI Optoelectronics offers two distinct families of UV enhanced silicon photodiodes. Inversion channel series and planar diffused series. Both families of devices are especially designed for low noise detection in the UV region of electromagnetic spectrum.

Inversion layer structure UV enhanced photodiodes exhibit 100% internal quantum efficiency and are well suited for low intensity light measurements. They have high shunt resistance, low noise and high breakdown voltages. The response uniformity across the surface and quantum efficiency improves with 5 to 10 volts applied reverse bias. In photovoltaic mode (unbiased), the capacitance is higher than diffused devices but decreases rapidly with an applied reverse bias. Photocurrent non-linearity sets in at lower photocurrents for inversion layer devices compared to the diffused ones. Below 700nm, their responsivities vary little with temperature.

Planar diffused structure UV enhanced photodiodes show significant advantages over inversion layer devices, such as lower capacitance and higher response time. These devices exhibit linearity of photocurrent up to higher light input power compared to inversion layer devices. They have relatively lower responsivities and quantum efficiencies compared to inversion layer devices

There are two types of planar diffused UV enhanced photodiodes available: UVDQ and UVEQ. Both series have almost similar electro-optical characteristics, except in the UVEQ series, where the near IR responses of the devices are suppressed. This is especially desirable if blocking the near IR region of the spectrum is necessary. UVDQ devices peak at 970 nm and UVEQ devices at 720 nm (see graph). Both series may be biased for lower capacitance, faster response and wider dynamic range. Or they may be operated in the photovoltaic (unbiased) mode for applications requiring low drift with temperature variations. The UVEQ devices have a higher shunt resistance than their counterparts of UVDQ devices, but have a higher capacitance.



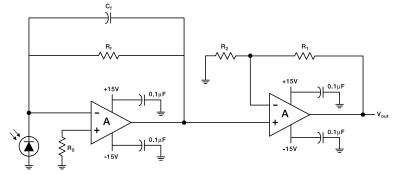
### **APPLICATIONS**

- Pollution Monitoring
- Medical Instrumentation
- UV Exposure Meters
- Spectroscopy
- Water Purification
- Fluorescence

#### **FEATURES**

- Inversion series:
   100% Internal QE
- Ultra High R<sub>SH</sub>
- Planar Diffused Series:
   IR Suppressed
   High Speed Response
   High Stability
- Excellent UV response

These detectors are ideal for coupling to an OP-AMP in the current mode configuration as shown.

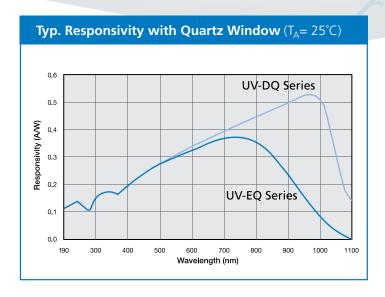


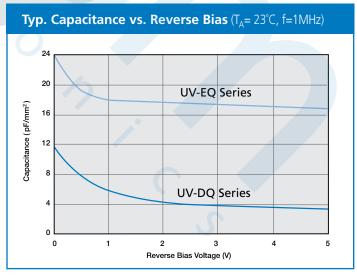
# **Planar Diffused UV Enhanced Photodiodes**

Typical Electro-Optical Specifications at T<sub>A</sub>=23°C

Model Number	Active Area		Peak	Responsivity (A/W)			Capacitance (pF)	Shunt Resistance (GOhm)		NEP (W/√Hz)	Reverse	Rise Time (µs)	Temp.* Range (°C)		
	Area (mm²)	Dimensions (mm)	Wavelength  λ P  (nm)	200 nm	633 nm typ.	Peak	0 V	-10 mV		0V 200 nm	Voltage (V)	0 V 1kOhm	Operating	Storage	Package Style ¶
							typ.	min.	typ.	typ.	max.	typ.	Ope	Stc	
UV-DQ' Se	ries P	lanar Di	ffused, Me	etal P	ackag	e, Qu	artz Windo	ow							
UV-005DQ	5.7	2.4 x 2.4	980	0.12	0.33	0.5	65	0.3	1	3.6 E-14	5	0.2		-55 ~ +80	5 / TO-5
UV-013DQ	13	3.6 x 3.6					150	0.2	0.8	4.1 E-14		0.5	09+		5 / TO-5
UV-035DQ	34	5.8 x 5.8					380	0.1	0.4	5.8 E-14		1	-20 ~		6 / TO-8
UV-100DQ	100	10 X 10					1100	0.04	0.2	8.2 E-14		3			11 /BNC
'UV-DQC' S	eries	Planar [	Diffused, C	eram	ic Pac	kage,	Quartz Wi	indow	/						
UV-005DQC	5.7	2.4 x 2.4	980			0.5	65	0.3	1	3.6 E-14	5	0.2	0	-20 ~ +80	
UV-035DQC	34	5.8 x 5.8		0.12	0.33		380	0.1	0.4	5.8 E-14		1	09+~(		25 / Ceramic
UV-100DQC	100	10 X 10					1100	0.04	0.2	8.2 E-14		3	-20		
UV-EQ' Sei	ries Pl	anar Di	ffused, Me	etal Pa	ackag	e, Qua	artz Windo	)W				'	, ,		
UV-005EQ	5.7	2.4 x 2.4	720	0.12	0.34	0.36	140	2	20	8.2 E-15	5	0.5		-55 ~ +80	5 / TO-5
UV-013EQ	13	3.6 x 3.6					280	1	10	1.1 E -14		1	09+		5 / TO-5
UV-035EQ	34	5.8 x 5.8					800	0.5	5	1.6 E -14		2	-20 ~		6 / TO-8
UV-100EQ	100	10 X 10					2500	0.2	2	2.6 E -14		7			11 /BNC
UV-EQC' S	eries I	Planar D	iffused, C	erami	ic Pacl	kage,	Quartz Wi	ndow				•			
UV-005EQC	5.7	2.4 x 2.4	720			0.36	140	2	20	8.2E-15	5	0.5	0	0	
UV-035EQC	34	5.8 x 5.8		0.12	0.34		800	0.5	5	1.6 E-14		2	-20 ~ +60	~ +80	25 / Ceramic
												7		-20	

<sup>¶</sup> For mechanical specifications please refer to pages 61 thru 73.
\* Non-Condensing temperature and Storage Range, Non-Condensing Environment.





## **Photodiode Care and Handling Instructions**

#### **AVOID DIRECT LIGHT**

Since the spectral response of silicon photodiode includes the visible light region, care must be taken to avoid photodiode exposure to high ambient light levels, particularly from tungsten sources or sunlight. During shipment from OSI Optoelectronics, your photodiodes are packaged in opaque, padded containers to avoid ambient light exposure and damage due to shock from dropping or jarring.

### **AVOID SHARP PHYSICAL SHOCK**

Photodiodes can be rendered inoperable if dropped or sharply jarred. The wire bonds are delicate and can become separated from the photodiode's bonding pads when the detector is dropped or otherwise receives a sharp physical blow.

#### CLEAN WINDOWS WITH OPTICAL GRADE CLOTH / TISSUE

Most windows on OSI Optoelectronics photodiodes are either silicon or quartz. They should be cleaned with isopropyl alcohol and a soft (optical grade) pad.

#### **OBSERVE STORAGE TEMPERATURES AND HUMIDITY LEVELS**

Photodiode exposure to extreme high or low storage temperatures can affect the subsequent performance of a silicon photodiode. Storage temperature guidelines are presented in the photodiode performance specifications of this catalog. Please maintain a non-condensing environment for optimum performance and lifetime.

### **OBSERVE ELECTROSTATIC DISCHARGE (ESD) PRECAUTIONS**

OSI Optoelectronics photodiodes, especially with IC devices (e.g. Photops) are considered ESD sensitive. The photodiodes are shipped in ESD protective packaging. When unpacking and using these products, anti-ESD precautions should be observed.

#### DO NOT EXPOSE PHOTODIODES TO HARSH CHEMICALS

Photodiode packages and/or operation may be impaired if exposed to CHLOROTHENE, THINNER, ACETONE, or TRICHLOROETHYLENE.

### **INSTALL WITH CARE**

Most photodiodes in this catalog are provided with wire or pin leads for installation in circuit boards or sockets. Observe the soldering temperatures and conditions specified below:

Soldering Iron: Soldering 30 W or less

Temperature at tip of iron 300°C or lower.

Dip Soldering: Bath Temperature: 260±5°C.

Immersion Time: within 5 Sec. Soldering Time: within 3 Sec.

Vapor Phase Soldering: DO NOT USE

Reflow Soldering: DO NOT USE

Photodiodes in plastic packages should be given special care. Clear plastic packages are more sensitive to environmental stress than those of black plastic. Storing devices in high humidity can present problems when soldering. Since the rapid heating during soldering stresses the wire bonds and can cause wire to bonding pad separation, it is recommended that devices in plastic packages to be baked for 24 hours at 85°C.

The leads on the photodiode **SHOULD NOT BE FORMED**. If your application requires lead spacing modification, please contact OSI Optoelectronics Applications group at (310)978-0516 before forming a product's leads. Product warranties could be voided.



\*Most of our standard catalog products are RoHS Compliant. Please contact us for details

### 1. Parameter Definitions:

- A = Distance from top of chip to top of glass.
- a = Photodiode Anode.
- B = Distance from top of glass to bottom of case.
- c = Photodiode Cathode
  - (Note: cathode is common to case in metal package products unless otherwise noted).
- W = Window Diameter.
- F.O.V. = Filed of View (see definition below).
- 2. Dimensions are in inches (1 inch = 25.4 mm).
- 3. Pin diameters are 0.018 ± 0.002" unless otherwise specified.
- 4. Tolerances (unless otherwise noted)

General: 0.XX ±0.01"

0.XXX ±0.005"

Chip Centering: ±0.010" Dimension 'A': ±0.015"

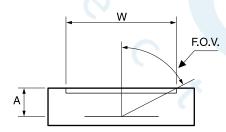
### 5. Windows

All 'UV' Enhanced products are provided with QUARTZ glass windows,  $0.027 \pm 0.002$ " thick.

All 'XUV' products are provided with removable windows.

All 'DLS' PSD products are provided with A/R coated glass windows.

All 'FIL' photoconductive and photovoltaic products are epoxy filled instead of glass windows.



$$F.O.V. = \tan^{-1}\left(\frac{W}{2A}\right)$$



For Further Assistance Please Call One of Our Experienced Sales and Applications Engineers

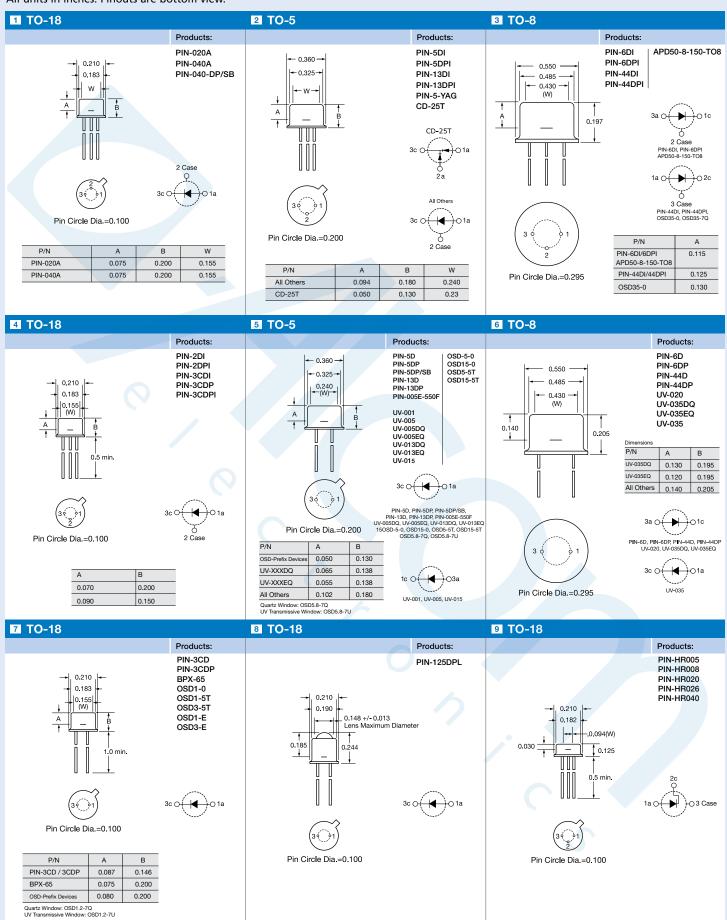
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- Or visit our website at
www.osioptoelectronics.com

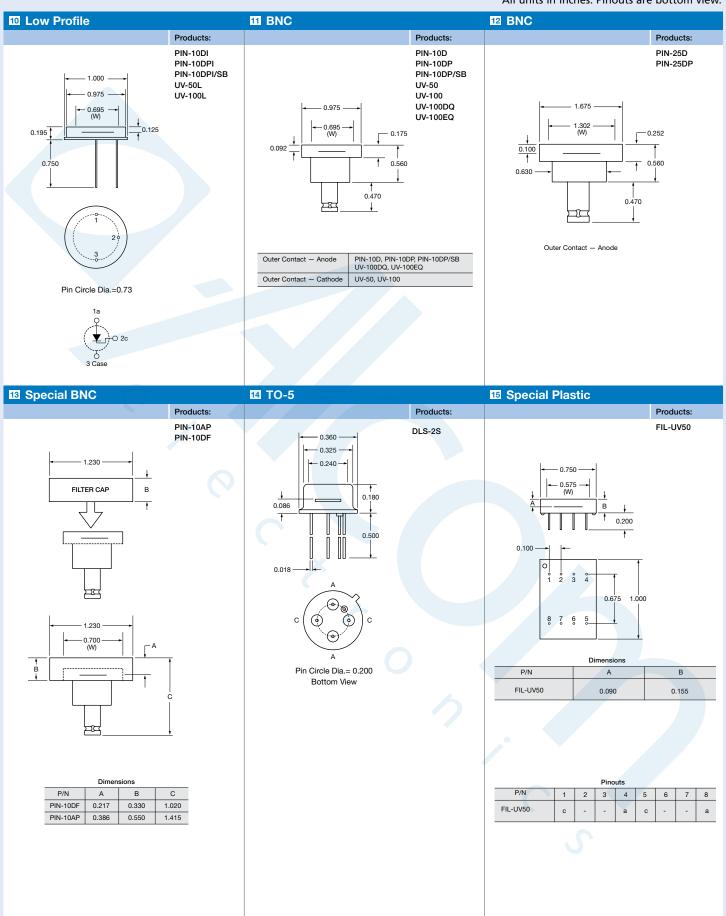
## **Mechanical Specifications**

All units in inches. Pinouts are bottom view.



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